



14N50

Power MOSFET

14A, 500V N-CHANNEL POWER MOSFET

DESCRIPTION

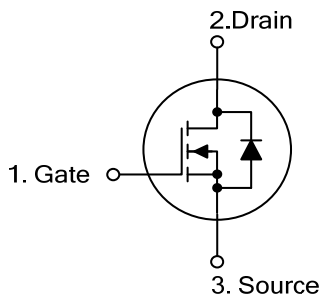
The UTC **14N50** is a N-Channel enhancement mode power MOSFET. The device adopts planar stripe and uses DMOS technology to minimize and provide lower on-state resistance and faster switching speed. It can also withstand high energy pulse under the avalanche and commutation mode conditions.

The UTC **14N50** is ideally suitable for high efficiency switch mode power supply, power factor correction and electronic lamp ballast based on half bridge topology.

FEATURES

- * $R_{DS(ON)} < 0.50 \Omega @ V_{GS} = 10V, I_D = 7.0A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL

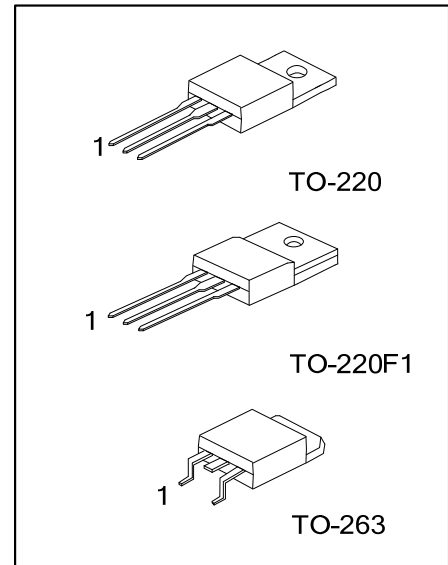


ORDERING INFORMATION

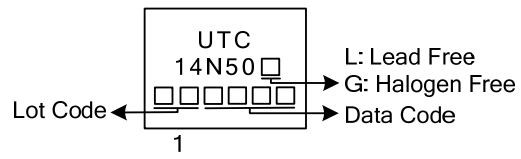
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
14N50L-TA3-T	14N50G-TA3-T	TO-220	G	D	S	Tube
14N50L-TF1-T	14N50G-TF1-T	TO-220F1	G	D	S	Tube
14N50L-TQ2-T	14N50G-TQ2-T	TO-263	G	D	S	Tube
14N50L-TQ2-R	14N50G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

14N50G-TA3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3 : TO-220, TF1: TO-220F1, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	500	V
Gate-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current	I_D	14	A
Pulsed Drain Current (Note 2)	I_{DM}	48	A
Avalanche Current (Note 2)	I_{AR}	14	A
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	400	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation ($T_C=25^\circ\text{C}$)	TO-220	P_D	150
	TO-220F1		50
	TO-263		150
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L = 9.3\text{mH}$, $I_{AS} = 13\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 13\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.83
	TO-220F1		2.5
	TO-263		0.83

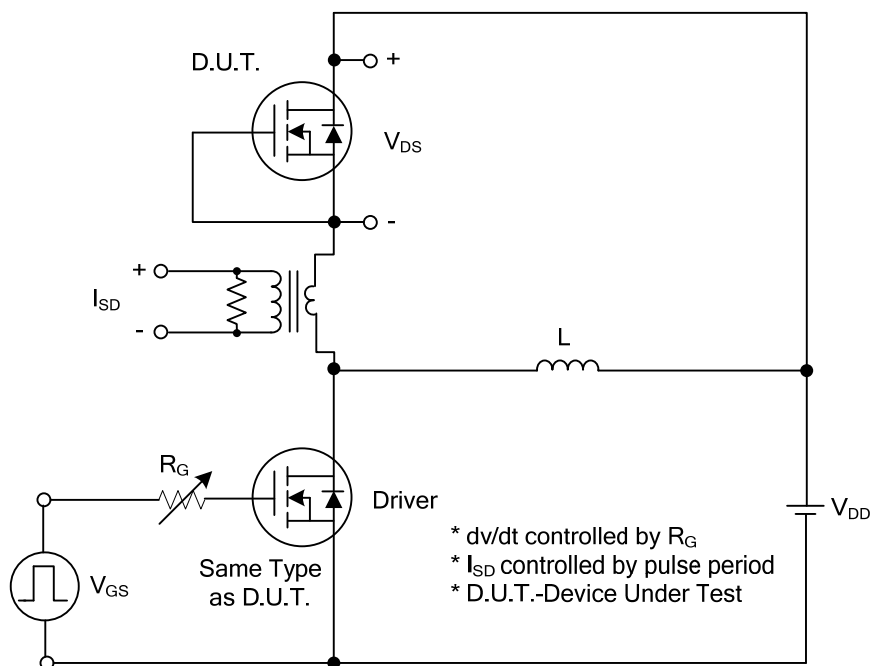
■ **ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 1mA	500			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 500V, V _{GS} = 0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = 20V, V _{DS} = 0V			100	nA
		V _{GS} = -20V, V _{DS} = 0V			-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250mA,Referenced to 25°C		0.5		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 100μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 7.0A			0.50	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		2000		pF
Output Capacitance	C _{OSS}			238		pF
Reverse Transfer Capacitance	C _{RSS}			55		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =400V, I _D =12A, V _{GS} =10 V (Note 1,2)		69	92	nC
Gate-Source Charge	Q _{GS}			12		nC
Gate-Drain Charge	Q _{GD}			31		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =250V, I _D =14A, R _G =25Ω (Note 1,2)		24		nS
Turn-On Rise Time	t _R			70		nS
Turn-Off Delay Time	t _{D(OFF)}			54		nS
Turn-Off Fall Time	t _F			50		nS
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 14A			1.6	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				14	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				56	A
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S = 14A,		470		nS
Reverse Recovery Charge	Q _{RR}	dl _F / dt =100A/μs (Note 1)		3.1		μC

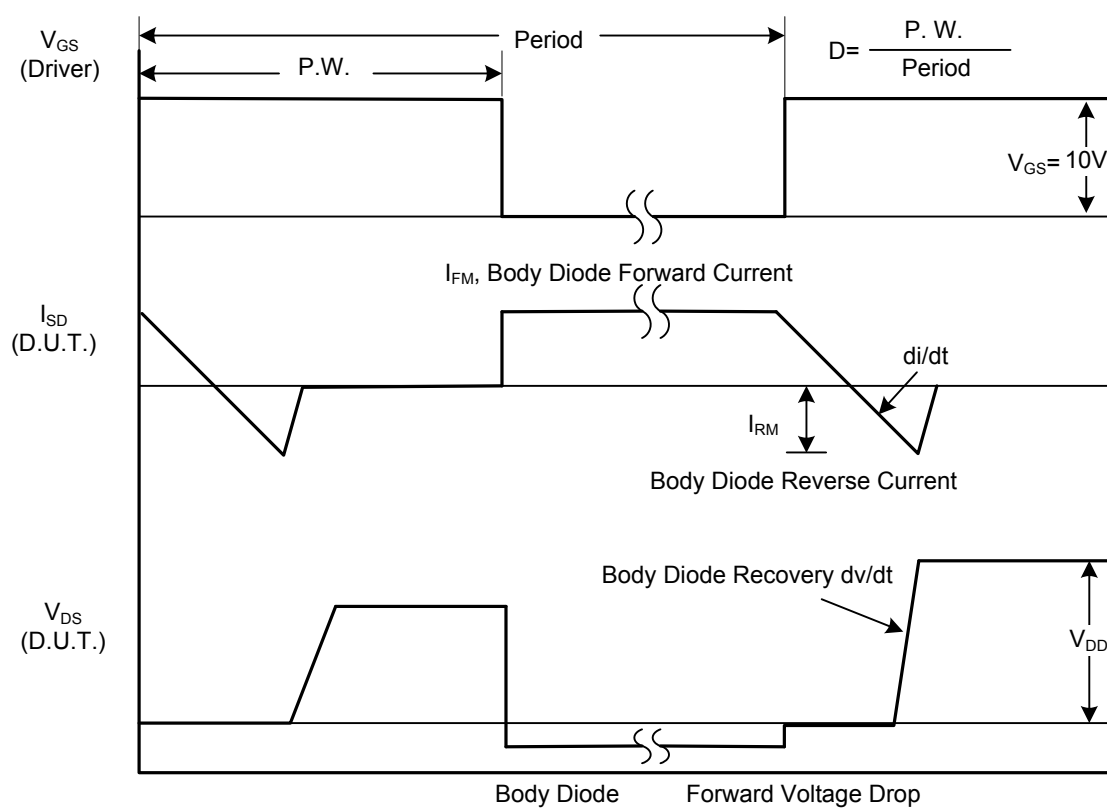
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

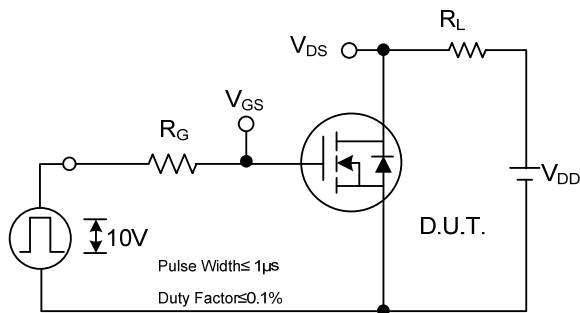


Peak Diode Recovery dv/dt Test Circuit

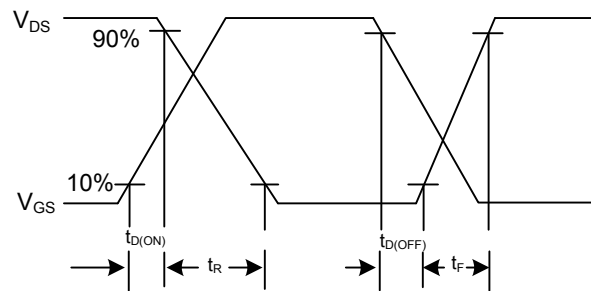


Peak Diode Recovery dv/dt Waveforms

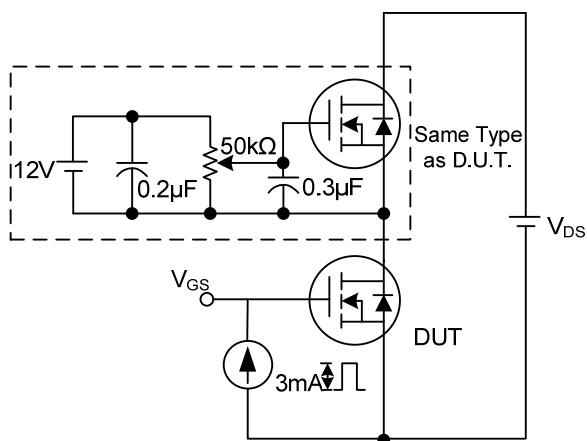
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



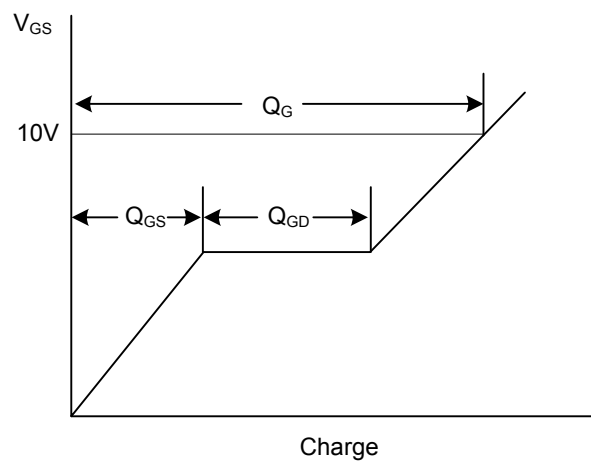
Switching Test Circuit



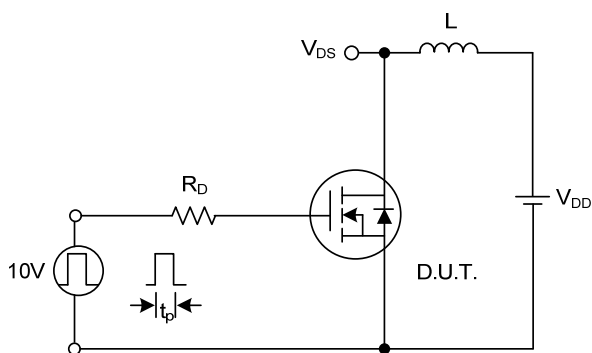
Switching Waveforms



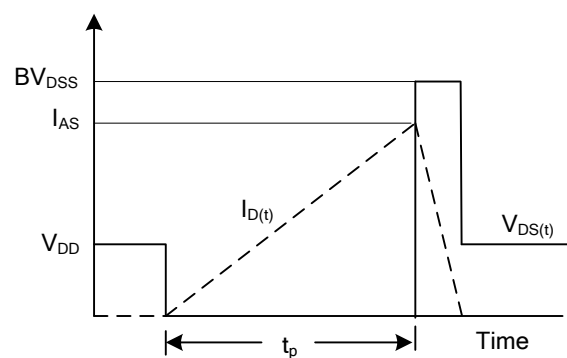
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

